

# **Session BB:**

## **Microwave Power Transistors**

**Chairman: Peter Staecker**

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Interest in extending the power capability and efficiency of power FETs has been matched only by that observed in areas of alternative 3-terminal device development. Current progress in FET technology is focused in this year's Symposium on C-Band internally matched devices, where power level of 30W have been obtained in an internally-matched configuration. Concurrent with device development are efforts to extend efficiency-improvement harmonic termination techniques to X-Band frequencies.

Progress in power HBTs has been marked during this year by efforts both at S- and Ku-band which qualify it as a contender for power device applications up to 18 GHz.

**8:00 a.m.–9:30 a.m., Thursday, May 10, 1990**  
**West Ballroom A, B**